

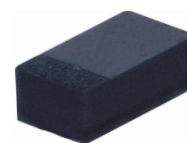
SMD Switching Diode

COMCHIP

SMD Diodes Specialist

CDSER400B (RoHs Device)

High Speed



Features

Designed for mounting on small surface.

Extremely thin/leadless package.

Low leakage current.

High mounting capability, strong surge withstand, high reliability.

Mechanical data

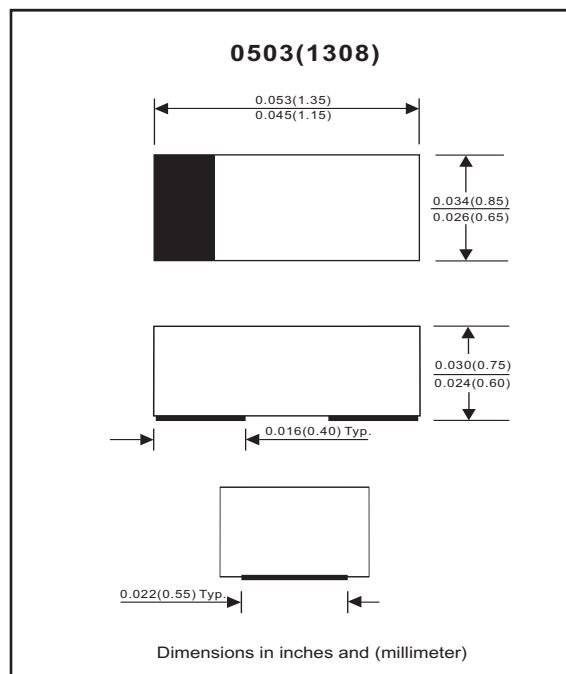
Case: 0503(1308) standard package, molded plastic.

Terminals: Gold plated, solderable per MIL-STD-750,method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any

Weight: 0.002 gram(approx.).



Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V_{RRM}			90	V
Reverse voltage		V_R			80	V
Average forward current		I_O			100	mA
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load (JEDEC method)	I_{FSM}		1000		mA
Repetitive peak forward current		I_{FRM}			225	mA
Power Dissipation		P_D			150	mW
Storage temperature		T_{STG}	-55		+125	°C
Junction temperature		T_j			+125	°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 100 \text{ mA DC}$	V_F			1.0	V
Reverse current	$V_R = 80 \text{ V}$	I_R			0.1	uA
Capacitance between terminals	$f = 1 \text{ MHz, and } 0.5 \text{ VDC reverse voltage}$	C_T			3	pF
Reverse recovery time	$V_R = 6 \text{ V, } I_F = 10 \text{ mA, } R_L = 50 \text{ ohms}$	T_{rr}			4	nS

REV:A

RATING AND CHARACTERISTIC CURVES (CDSER400B)

Fig. 1 - Forward characteristics

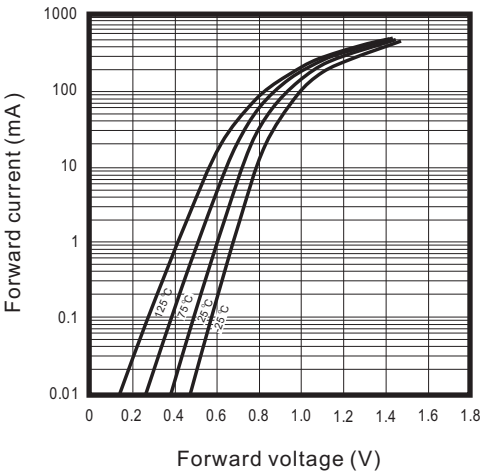


Fig. 2 - Reverse characteristics

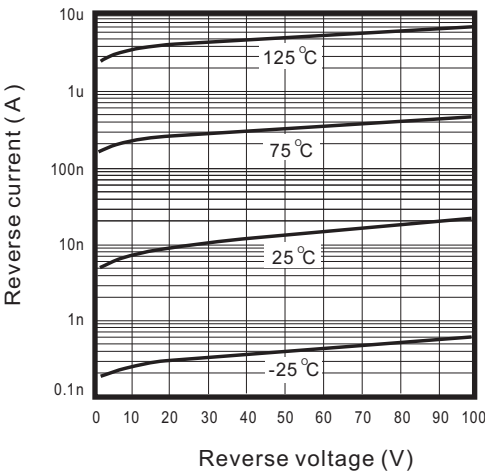


Fig. 3 - Capacitance between terminals characteristics

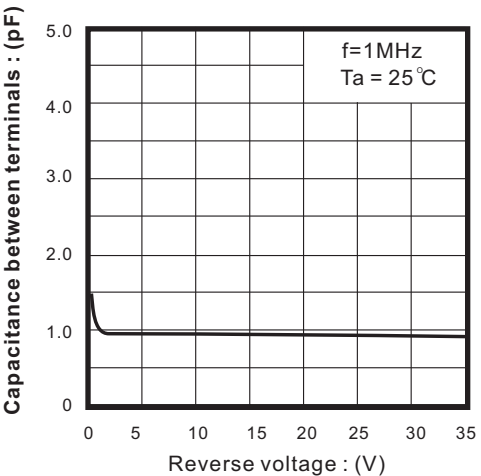


Fig. 4 - Current derating curve

